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April 2013

# FAN7527B Power Factor Correction Controller

#### **Features**

- Internal Startup Timer
- Internal R/C Filter Eliminates the Need for External R/C Filter
- Precise Adjustable Output Over-Voltage Protection
- Zero Current Detector
- One Quadrant Multiplier
- Trimmed 1.5% Internal Band Gap Reference
- Under-Voltage Lockout with 3 V of Hysteresis
- Totem-Pole Output with High-State Clamp
- Low Startup and Operating Current
- 8-Pin SOP or 8-Pin DIP

#### **Applications**

- Electronic Ballast
- SMPS

#### **Description**

The FAN7527B provides simple and high-performance active Power Factor Correction (PFC). The FAN7527B is optimized for electronic ballasts and low-power, high-density power supplies that require minimum board size, reduced external components, and low power dissipation. Because the R/C filter is included in the current-sense block, an external R/C filter is not necessary. Special circuitry prevents no-load runaway conditions. Regardless of the supply voltage, the output drive clamping circuit limits the overshoot of the power MOSFET gate drive, which improves system reliability.



#### **Ordering Information**

Part Number	Operating Temperature Range	Package	Packing Method
FAN7527BMX	-25 to +125°C	8-Lead, Small Outline Package (SOP)	Tape and Reel
FAN7527BN	-25 to +125°C	8-Lead, Dual Inline Package (DIP)	Tube

## **Block Diagram**

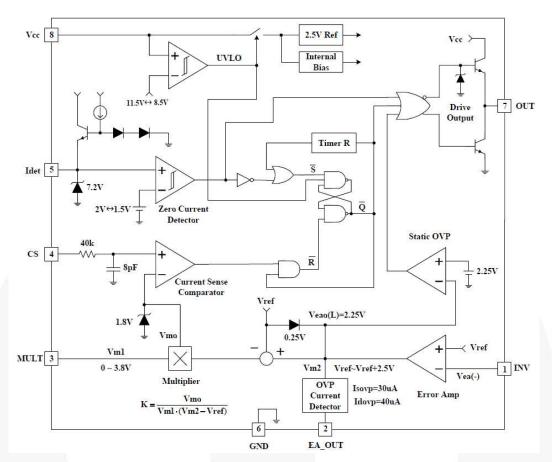


Figure 1. Block Diagram

## **Pin Configuration**

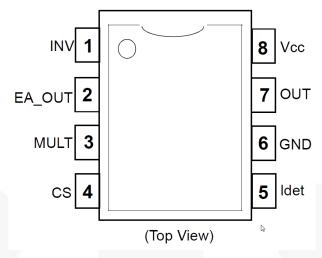


Figure 2. Pin Configuration

## **Pin Definitions**

Pin#	Name	Description
1	INV	Inverting input of the error amplifier. The output of the boost converter should be resistively divided to 2.5 V and connected to this pin.
2	EA_OUT	Output of the error amplifier. Feedback compensation network is placed between this pin and the INV pin.
3	MULT	Input to the multiplier stage. The full-wave rectified AC voltage is divided to less than 2 V and is connected to this pin.
4	CS	Input of the PWM comparator. The MOSFET current is sensed by a resistor and the resulting voltage is applied to this pin. An internal R/C filter is included to reject high-frequency noise.
5	Idet	Zero Current Detection (ZCD) input.
6	GND	Ground
7	OUT	Gate driver output. Push-pull output stage is able to drive the power MOSFET with a peak current of 500 mA.
8	V <sub>CC</sub>	Supply voltage of driver and control circuits.

## **Absolute Maximum Ratings**

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter			Max.	Unit
V <sub>CC</sub>	Supply Voltage			30	V
I <sub>OH</sub> , I <sub>OL</sub>	Peak Drive Output Current			±500	mA
I <sub>CLAMP</sub>	Driver Output Clamping Diodes V <sub>O</sub> > V <sub>C</sub>	<sub>C</sub> or V <sub>O</sub> <-0.3 V		±10	mA
I <sub>DET</sub>	Detector Clamping Diodes			±10	mA
V <sub>IN</sub>	Error Amplifier Multiplier and Comparator Input Voltages		-0.3	6.0	V
TJ	Operation Junction Temperature			+150	°C
T <sub>OPR</sub>	Operating Temperature Range		-25	+125	°C
T <sub>STG</sub>	Storage Temperature Range		-65	+150	°C
ь //	Power Dissipation	8-SOP		0.8	W
P <sub>D</sub>		8-DIP		1.1	W
0	Thermal Resistance Junction-Ambient	8-SOP		150	°C/W
$\Theta_{JA}$		8-DIP		110	°C/W

#### **Temperature Characteristics**

-25°C  $\leq T_A \leq 125$ °C.

Symbol	Parameter	Min.	Тур.	Max.	Unit
$\Delta V_{REF}$	Temperature Stability Reference Voltage (V <sub>REF</sub> )		20		mV
ΔΚ/ΔΤ	Temperature Stability for Multiplier Gain (K)		-0.2		%/°C

### **Electrical Characteristics**

 $V_{CC}$ = 14 V, -25°C ≤  $T_A$  ≤ 125°C, unless otherwise stated.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Under-Volta	ge Lockout		•		•	•
$V_{th(st)}$	Start Threshold Voltage	V <sub>CC</sub> Increasing	10.5	11.5	12.5	V
H <sub>Y(st)</sub>	UVLO Hysteresis		2	3	4	V
Supply Curr	ent Section		•		•	•
I <sub>ST</sub>	Startup Supply Current	$V_{CC} = V_{th(st)} - 0.2 \text{ V}$	10	60	100	μΑ
I <sub>CC</sub>	Operating Supply Current	Output Not Switching		3	6	mA
I <sub>CC(OVP)</sub>	Operating Current at OVP	V <sub>INV</sub> = 3 V		1.7	4.0	mA
I <sub>DCC</sub>	Dynamic Operating Supply Current	50 kHz, C <sub>I</sub> = 1 nF	1	4	8	mA
Error Ampli	fier Section					•
V	Note of Fourth and James Theory	I <sub>REF</sub> = 0 mA, T <sub>A</sub> = 25°C	2.465	2.500	2.535	.,
$V_{REF}$	Voltage Feedback Input Threshold	25°C ≤ T <sub>A</sub> ≤ 125°C	2.440	2.500	2.560	V
$\Delta V_{FEF1}$	Line Regulation	14 V ≤ V <sub>CC</sub> ≤ 25 V		0.1	10.0	mV
$\Delta V_{FEF3}$	Temperature Stability of V <sub>REF</sub> <sup>(1)</sup>	-25°C ≤ T <sub>A</sub> ≤ 125°C		20		mV
I <sub>b(ea)</sub>	Input Bias Current		-0.5		0.5	μΑ
I <sub>SOURCE</sub>	Output Source Current	V <sub>M2</sub> = 4 V	-2	-4		mA
I <sub>SINK</sub>	Output Sink Current	$V_{M2} = 4 V$	2	4		mA
$V_{EAO(H)}$	Output Upper Clamp Voltage <sup>(1)</sup>	I <sub>SOURCE</sub> = 0.1 mA		6		V
$V_{EAO(L)}$	Output Lower Clamp Voltage <sup>(1)</sup>	I <sub>SINK</sub> = 0.1 mA		2.25		V
G <sub>V</sub>	Large Signal Open-Loop Gain <sup>(1)</sup>	y y	60	80		dB
PSRR	Power Supply Rejection Ratio <sup>(1)</sup>	14 V ≤ V <sub>CC</sub> ≤ 25 V	60	80		dB
GBW	Unity Gain Bandwidth <sup>(1)</sup>			1		MHZ
SR	Slew Rate <sup>(1)</sup>			0.6		V/µs
Multiplier Se	ection					
I <sub>b(m)</sub>	Input Bias Current (Pin 3)		-0.5		0.5	μΑ
$\Delta V_{M1}$	M1 Input Voltage Range (Pin 3)				3.8	V
$\Delta V_{M2}$	M2 Input Voltage Range (Pin 2)		$V_{REF}$		V <sub>REF</sub> +2.5	V
K	Multiplier Gain <sup>(1)</sup>	$V_{M1} = 1 \ V, \ V_{M2} = 3.5 \ V$	0.36	0.44	0.52	1 / V
$V_{OMAX(m)}$	Maximum Multiplier Output Voltage	$V_{INV} = 0 \ V, \ V_{M1} = 4 \ V$	1.65	1.80	1.95	V
ΔΚ/ΔΤ	Temperature Stability of K <sup>(1)</sup>	-25 ≤ T <sub>A</sub> ≤ 125°C		-0.2	M	%/°C
Current Sen	se Section					
V <sub>IO(CS)</sub>	Input Offset Voltage <sup>(1)</sup>	$V_{M1} = 0 \ V, \ V_{M2} = 2.2 \ V$	-10	3	10	mV
I <sub>b(CS)</sub>	Input Bias Current	0 V ≤ V <sub>CS</sub> ≤ 1.7 V	-1.0	-0.1	1.0	μΑ
t <sub>D(CS)</sub>	Current Sense Delay to Output <sup>(1)</sup>			200	500	ns

Continued on the following page...

#### **Electrical Characteristics** (Continued)

 $V_{CC}$ = 14 V, -25°C ≤  $T_A$  ≤ 125°C, unless otherwise stated.

Parameter	Conditions	Min.	Тур.	Max.	Unit	
Zero Current Detect Section						
Input Voltage Threshold	V <sub>DET</sub> Increasing	1.7	2.0	2.3	V	
Detect Hysteresis		0.2	0.5	0.8	V	
Input Low Clamp Voltage	$I_{DET} = -100 \mu A$	0.45	0.75	1.00	٧	
Input High Clamp Voltage	I <sub>DET</sub> = 3 mA	6.5	7.2	7.9	V	
Input Bias Current	1 V ≤ V <sub>DET</sub> ≤ 5 V	-1.0	-0.1	1.0	μΑ	
Input High/Low Clamp Diode Current <sup>(1)</sup>				±3	mA	
ion						
Output Voltage High	I <sub>O</sub> = -10 mA	10.5	11.0		V	
Output Voltage Low	I <sub>O</sub> = 10 mA		0.8	1.0	V	
Rising Time <sup>(1)</sup>	C <sub>L</sub> = 1 nF		130	200	ns	
Falling Time <sup>(1)</sup>	C <sub>L</sub> = 1 nF		50	120	ns	
Maximum Output Voltage	$V_{CC} = 20 \text{ V}, I_{O} = 100 \mu\text{A}$	12	14	16	V	
Output Voltage with UVLO Activated	$V_{CC} = 5 \text{ V}, I_{O} = 100 \mu\text{A}$		N.	1	٧	
er Section						
Restart Time Delay	$V_{M1} = 1 \text{ V}, V_{M2} = 3.5 \text{ V}$		150		μs	
Over-Voltage Protection Section						
Soft OVP Detecting Current		25	30	35	μΑ	
Dynamic OVP Detecting Current		35	40	45	μΑ	
Static OVP Threshold Voltage	$V_{INV} = 2.7 \text{ V}$	2.10	2.25	2.40	V	
	Input Voltage Threshold Detect Hysteresis Input Low Clamp Voltage Input High Clamp Voltage Input Bias Current Input High/Low Clamp Diode Current(1)  ion Output Voltage High Output Voltage Low Rising Time(1) Falling Time(1) Maximum Output Voltage Output Voltage with UVLO Activated er Section Restart Time Delay e Protection Section Soft OVP Detecting Current Dynamic OVP Detecting Current	t Detect Section  Input Voltage Threshold VDET Increasing  Detect Hysteresis  Input Low Clamp Voltage IDET = -100 μA  Input High Clamp Voltage IDET = 3 mA  Input Bias Current 1 V ≤ VDET ≤ 5 V  Input High/Low Clamp Diode Current IDET = 10 mA  Output Voltage High IDET = 10 mA  Output Voltage Low IDET = 10 mA  Rising Time IDET = 20 V, IDET ≤ 5 V  Input High/Low Clamp Diode Current IDET = 10 mA  Output Voltage High IDET = 10 mA  Output Voltage Low IDET = 10 mA  Rising Time IDET = 10 mA  Value = 100 μA  Value = 100	t Detect Section  Input Voltage Threshold V <sub>DET</sub> Increasing 1.7  Detect Hysteresis 0.2  Input Low Clamp Voltage I <sub>DET</sub> = -100 μA 0.45  Input High Clamp Voltage I <sub>DET</sub> = 3 mA 6.5  Input Bias Current 1 V ≤ V <sub>DET</sub> ≤ 5 V -1.0  Input High/Low Clamp Diode Current(1)  ion  Output Voltage High I <sub>O</sub> = -10 mA 10.5  Output Voltage Low I <sub>O</sub> = 10 mA  Rising Time(1) C <sub>L</sub> = 1 nF  Falling Time(1) C <sub>L</sub> = 1 nF  Maximum Output Voltage V <sub>CC</sub> = 20 V, I <sub>O</sub> = 100 μA 12  Output Voltage with UVLO Activated V <sub>CC</sub> = 5 V, I <sub>O</sub> = 100 μA 12  Protection Section  Soft OVP Detecting Current 25  Dynamic OVP Detecting Current 35	t Detect Section  Input Voltage Threshold $V_{DET}$ Increasing 1.7 2.0  Detect Hysteresis 0.2 0.5  Input Low Clamp Voltage $I_{DET} = -100  \mu A$ 0.45 0.75  Input High Clamp Voltage $I_{DET} = 3  \text{mA}$ 6.5 7.2  Input Bias Current 1 $V \le V_{DET} \le 5  V$ -1.0 -0.1  Input High/Low Clamp Diode Current(1)  Output Voltage High $I_{O} = -10  \text{mA}$ 10.5 11.0  Output Voltage Low $I_{O} = 10  \text{mA}$ 0.8  Rising Time(1) $I_{O} = 10  \text{mA}$ 0.8  Rising Time(1) $I_{O} = 10  \text{mA}$ 1.30  Falling Time(1) $I_{O} = 10  \text{mA}$ 1.2 14  Output Voltage with UVLO $I_{O} = 100  \mu A$ 1.2 14  Output Voltage with UVLO $I_{O} = 100  \mu A$ 1.50  Restart Time Delay $I_{O} = 100  \mu A$ 1.50  Protection Section  Soft OVP Detecting Current 2.5 30  Dynamic OVP Detecting Current 3.5 40	t Detect Section    Input Voltage Threshold   V_{DET} Increasing   1.7   2.0   2.3     Detect Hysteresis   0.2   0.5   0.8     Input Low Clamp Voltage   I_{DET} = -100 μA   0.45   0.75   1.00     Input High Clamp Voltage   I_{DET} = 3 mA   6.5   7.2   7.9     Input Bias Current   1 ∨ ≤ V_{DET} ≤ 5 ∨   -1.0   -0.1   1.0     Input High/Low Clamp Diode   ±3     Ionut Voltage High   I_O = -10 mA   10.5   11.0     Output Voltage Low   I_O = 10 mA   0.8   1.0     Rising Time <sup>(1)</sup>   C <sub>L</sub> = 1 nF   130   200     Falling Time <sup>(1)</sup>   C <sub>L</sub> = 1 nF   50   120     Maximum Output Voltage   V <sub>CC</sub> = 20 ∨, I_O = 100 μA   12   14   16     Output Voltage with UVLO   V <sub>CC</sub> = 5 ∨, I_O = 100 μA   1     Per Section   Restart Time Delay   V <sub>M1</sub> = 1 ∨, V <sub>M2</sub> = 3.5 ∨   150     Protection Section   Soft OVP Detecting Current   25   30   35     Dynamic OVP Detecting Current   35   40   45     Output Voltage Current   35   40   45     Output OVP Detecting Current   35   40   45     Output Over D	

#### Note:

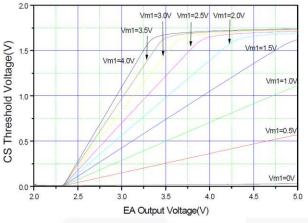
1. These parameters, although guaranteed, are not 100% tested in production.

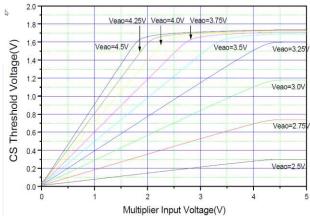
Multiplier Gain:

$$K = \frac{Pin4\_Threshold}{V_{M1} \times \left(V_{M2} - V_{REF}\right)}$$

where  $V_{M1} = V_{PIN3}$ ,  $V_{M2} = V_{PIN2}$ 

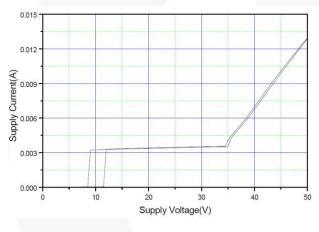
### **Typical Performance Characteristics**





Error Amplifier Output Voltage vs. Figure 3. **Current Sensing Threshold** 

Multiplier Input Voltage vs. Current Figure 4. Sensing Threshold



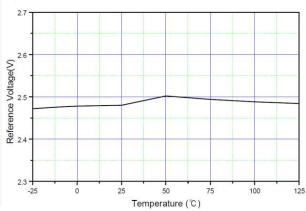
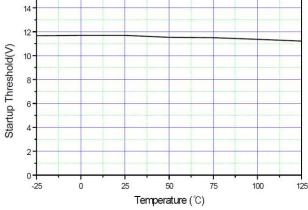
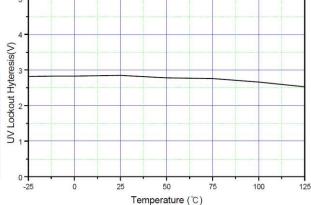


Figure 5. Supply Current vs. Supply Voltage

Figure 6.



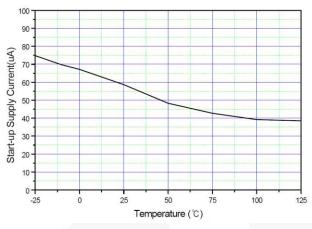


Reference Voltage vs. Temperature

Figure 7. Startup Threshold vs. Temperature

**UVLO Hysteresis vs. Temperature** Figure 8.

### **Typical Performance Characteristics** (Continued)



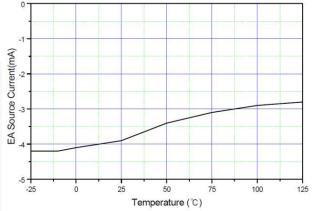
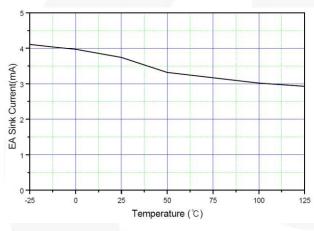


Figure 9. Startup Supply Current vs. Temperature

Figure 10. Error Amplifier Source Current



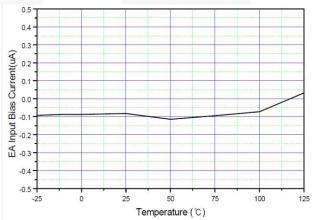
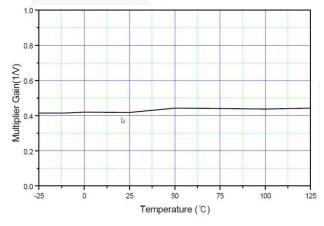


Figure 11. Error Amplifier Sink Current vs. Temperature

Figure 12. Error Amplifier Input Bias Current vs. Temperature



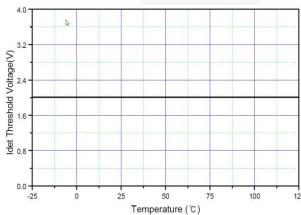
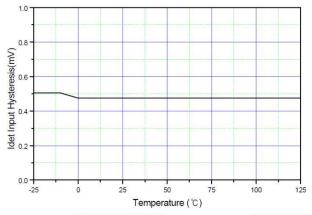


Figure 13. Multiplier Gain vs. Temperature

Figure 14. I<sub>DET</sub> Threshold Voltage vs. Threshold

## **Typical Performance Characteristics** (Continued)



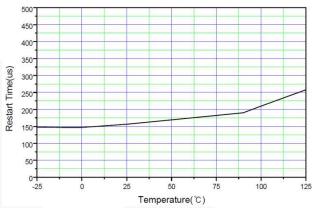
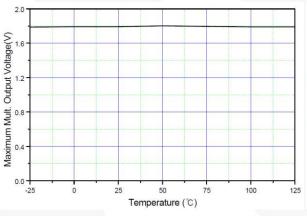


Figure 15. IDET Input Hysteresis vs. Temperature

Figure 16. Restart Time vs. Temperature



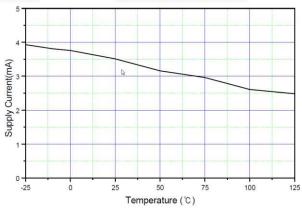
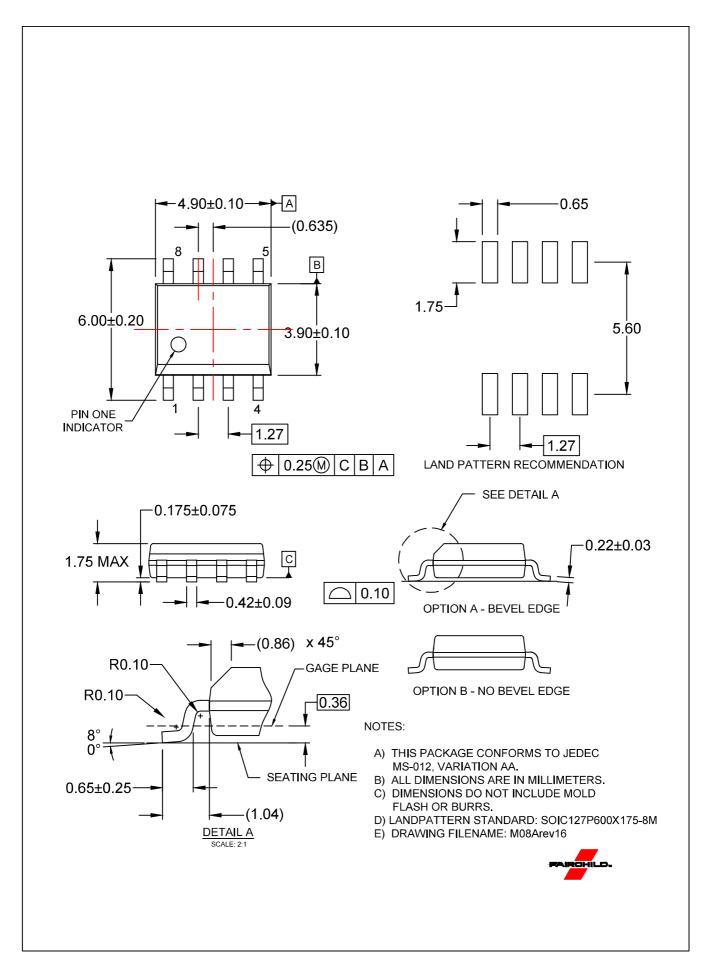
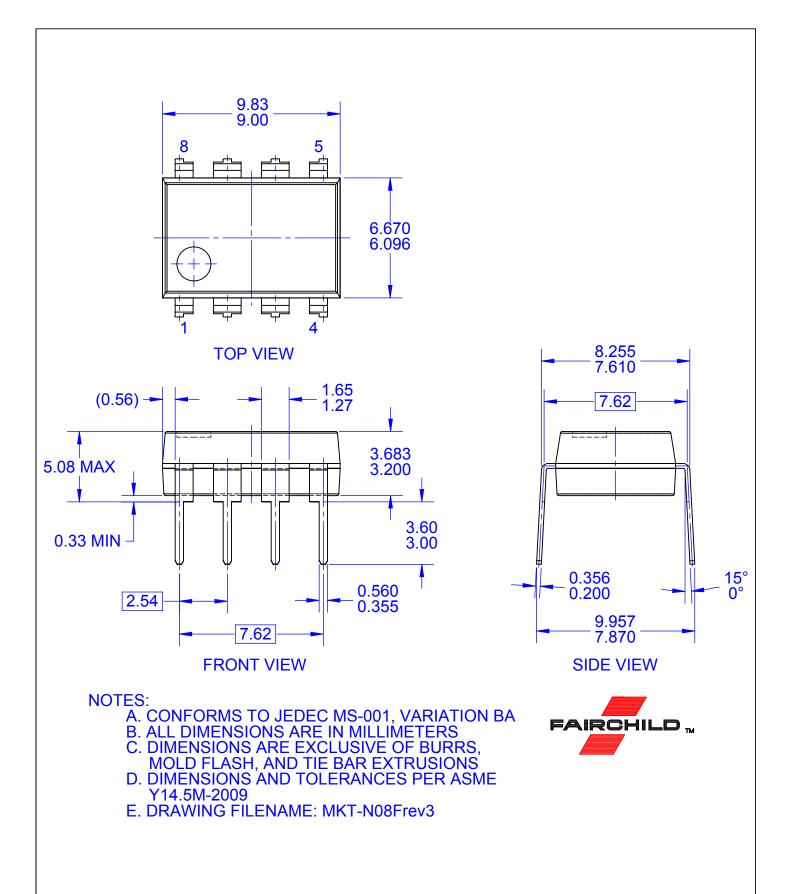


Figure 17. Maximum Multiplier Output Voltage vs. Temperature

Figure 18. Supply Current vs. Temperature





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